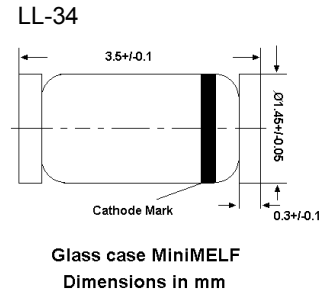


LL916, LL916A, LL916B

Silicon Epitaxial Planar Switching Diode

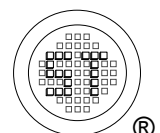


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current	I_{FSM}	1	A
at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$		4	
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 200	$^\circ\text{C}$

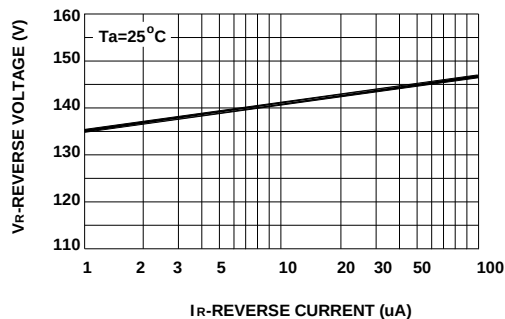
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$ at $I_R = 5\text{ }\mu\text{A}$	$V_{(BR)R}$	100 75	- -	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_j = 150^\circ\text{C}$	I_R	- - -	25 5 50	nA μA μA
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 20\text{ mA}$ at $I_F = 30\text{ mA}$	V_F V_F V_F V_F	0.63 - - -	0.73 1 1 1	V
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$ (60 mA), $I_{RR} = 1\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns

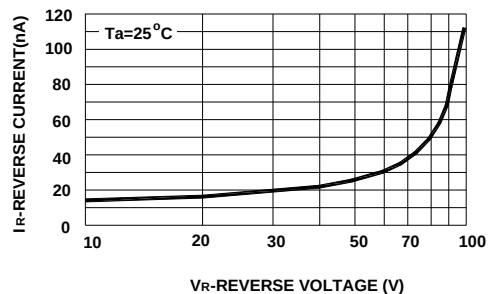


LL916, LL916A, LL916B

REVERSE VOLTAGE vs REVERSE CURRENT
BV-1.0 to 100 μ A

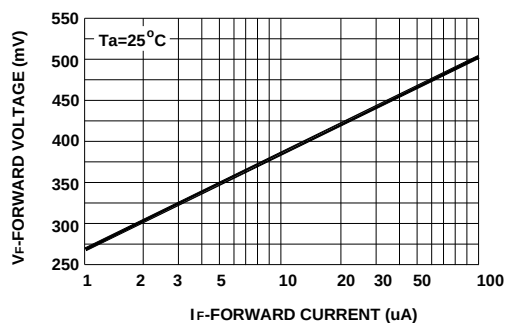


REVERSE CURRENT vs REVERSE VOLTAGE
 I_R -10 to 100 V

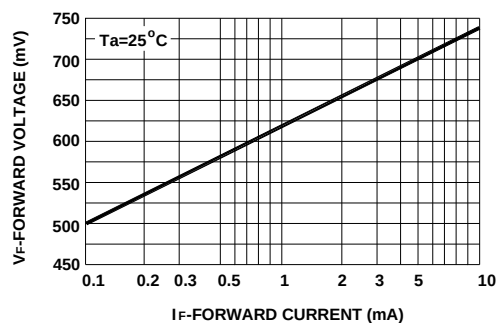


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

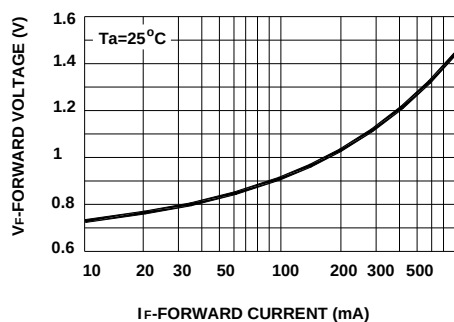
FORWARD VOLTAGE vs FORWARD CURRENT
 V_F -1 to 100 μ A



FORWARD VOLTAGE vs FORWARD CURRENT
 V_F -0.1 to 100 mA



FORWARD VOLTAGE vs FORWARD CURRENT
 V_F -10 to 800 mA



FORWARD VOLTAGE vs AMBIENT TEMPERATURE
 V_F -0.01 - 20 mA (-40 to +65 Deg C)

